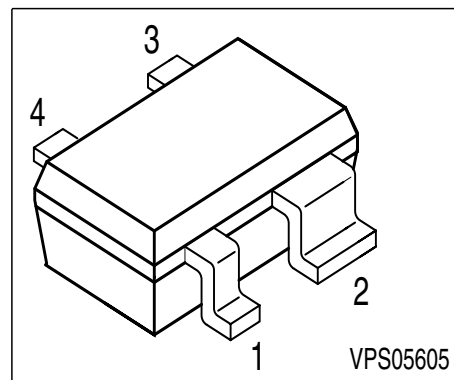


NPN Silicon RF Transistor

- For highest gain low noise amplifier at 1.8 GHz
- Outstanding $G_{ms} = 21$ dB
Noise Figure $F = 0.9$ dB
- Gold metallization for high reliability
- SIEGET 45 - Line



ESD: Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFP540	ATs	1=B	2=E	3=C	4=E	-	-	SOT343

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	4.5	V
Collector-emitter voltage	V_{CES}	14	
Collector-base voltage	V_{CBO}	14	
Emitter-base voltage	V_{EBO}	1	
Collector current	I_C	80	mA
Base current	I_B	8	
Total power dissipation ¹⁾ $T_S \leq 77^\circ\text{C}$	P_{tot}	250	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R_{thJS}	≤ 290	K/W

¹⁾ T_S is measured on the collector lead at the soldering point to the pcb

²⁾ For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	4.5	5	-	V
Collector-emitter cutoff current $V_{CE} = 14\text{ V}, V_{BE} = 0$	I_{CES}	-	-	10	μA
Collector-base cutoff current $V_{CB} = 5\text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 0.5\text{ V}, I_C = 0$	I_{EBO}	-	-	10	μA
DC current gain $I_C = 20\text{ mA}, V_{CE} = 3.5\text{ V}$	h_{FE}	50	110	200	-

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

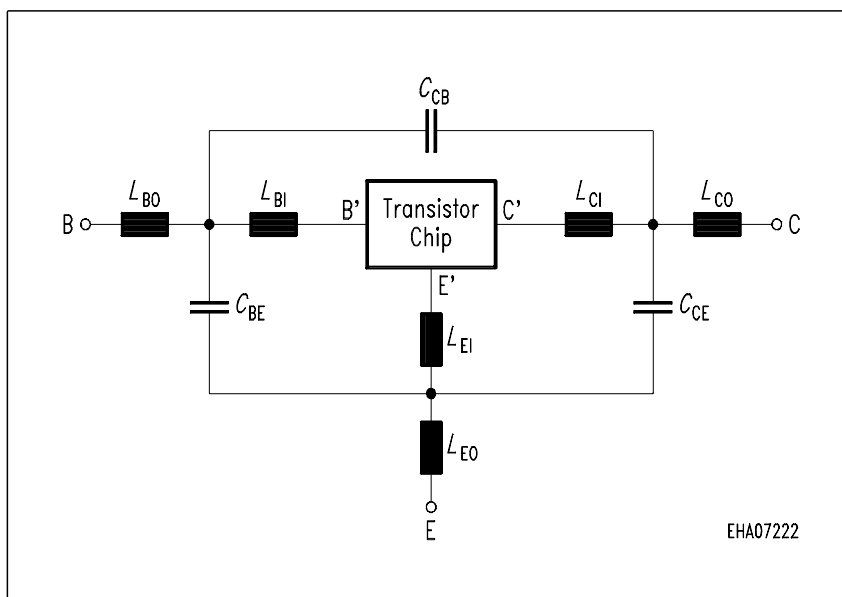
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 50\text{ mA}$, $V_{CE} = 4\text{ V}$, $f = 1\text{ GHz}$	f_T	21	30	-	GHz
Collector-base capacitance $V_{CB} = 2\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	0.14	0.24	pF
Collector emitter capacitance $V_{CE} = 2\text{ V}$, $f = 1\text{ MHz}$	C_{ce}	-	0.33	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{eb}	-	0.65	-	
Noise figure $I_C = 5\text{ mA}$, $V_{CE} = 2\text{ V}$, $f = 1.8\text{ GHz}$, $Z_S = Z_{Sopt}$ $I_C = 5\text{ mA}$, $V_{CE} = 2\text{ V}$, $f = 3\text{ GHz}$, $Z_S = Z_{Sopt}$	F	- -	0.9 1.3	1.4 -	dB
Power gain, maximum stable ¹⁾ $I_C = 20\text{ mA}$, $V_{CE} = 2\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$	G_{ms}	-	21.5	-	dB
Power gain, maximum available ¹⁾ $I_C = 20\text{ mA}$, $V_{CE} = 2\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 3\text{ GHz}$	G_{ma}	-	16	-	dB
Transducer gain $I_C = 20\text{ mA}$, $V_{CE} = 2\text{ V}$, $Z_S = Z_L = 50\text{ }\Omega$, $f = 1.8\text{ GHz}$ $I_C = 20\text{ mA}$, $V_{CE} = 2\text{ V}$, $Z_S = Z_L = 50\text{ }\Omega$, $f = 3\text{ GHz}$	$ S_{21e} ^2$	16 -	18.5 14.5	- -	dB
Third order intercept point at output ²⁾ $V_{CE} = 2\text{ V}$, $I_C = 20\text{ mA}$, $f = 1.8\text{ GHz}$, $Z_S = Z_L = 50\text{ }\Omega$	IP_3	-	24.5	-	dBm
1dB Compression point at output $I_C = 20\text{ mA}$, $V_{CE} = 2\text{ V}$, $Z_S = Z_L = 50\text{ }\Omega$, $f = 1.8\text{ GHz}$	P_{-1dB}	-	11	-	

¹⁾ $G_{ma} = |S_{21e} / S_{12e}| (k - (k^2 - 1)^{1/2})$, $G_{ms} = |S_{21e} / S_{12e}|$
²⁾ IP_3 value depends on termination of all intermodulation frequency components.
Termination used for this measurement is $50\ \Omega$ from 0.1 MHz to 6 GHz

SPICE Parameter (Gummel-Poon Model, Berkley-SPICE 2G.6 Syntax):
Transistor Chip Data:

IS =	82.84	aA	BF =	107.5	-	NF =	1	-
VAF =	28.383	V	IKF =	0.48731	A	ISE =	11.15	fA
NE =	3.19	-	BR =	5.5	-	NR =	1	-
VAR =	19.705	V	IKR =	0.02	A	ISC =	19.237	aA
NC =	1.172	-	RB =	5.4	Ω	IRB =	0.72983	mA
RBM =	1.3	Ω	RE =	0.31111	-	RC =	4	Ω
CJE =	1.8063	fF	VJE =	0.8051	V	MJE =	0.46576	-
TF =	6.76	ps	XTF =	0.4219	-	VTF =	0.23794	V
ITF =	1	mA	PTF =	0	deg	CJC =	234	fF
VJC =	0.81969	V	MJC =	0.30232	-	XCJC =	0.3	-
TR =	2.324	ns	CJS =	0	fF	VJS =	0.75	V
MJS =	0	-	XTB =	0	-	EG =	1.11	eV
XTI =	3	-	FC =	0.73234		TNOM	300	K

All parameters are ready to use, no scaling is necessary.

Package Equivalent Circuit:


L_{BI} =	0.47	nH
L_{BO} =	0.53	nH
L_{EI} =	0.23	nH
L_{EO} =	0.05	nH
L_{CI} =	0.56	pH
L_{EO} =	0.58	nH
C_{BE} =	136	fF
C_{CB} =	6.9	fF
C_{CE} =	134	fF

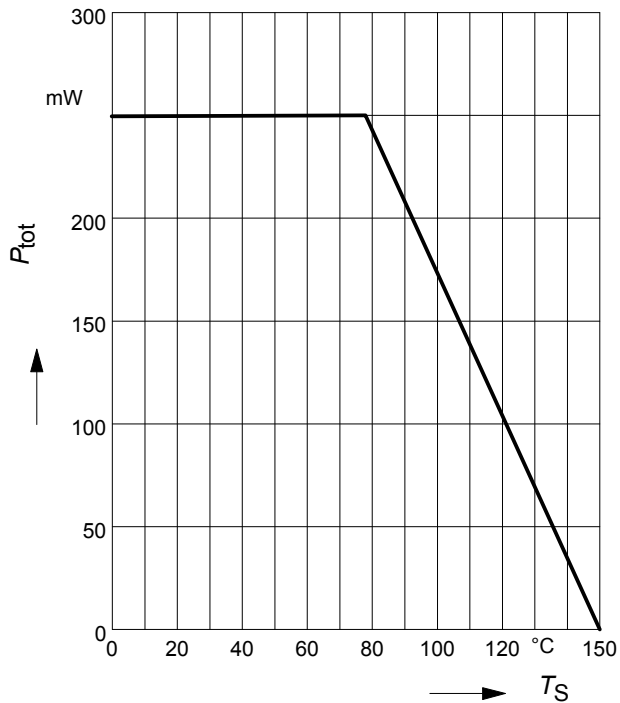
Valid up to 6GHz

For examples and ready to use parameters please contact your local Infineon Technologies distributor or sales office to obtain a Infineon Technologies CD-ROM or see Internet: <http://www.infineon.com/silicondiscretes>

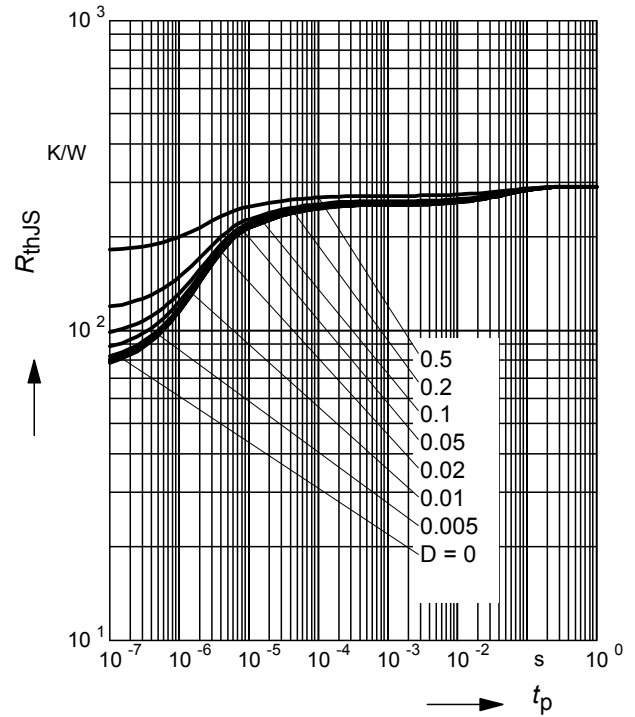
For non-linear simulation:

- Use transistor chip parameters in Berkeley SPICE 2G.6 syntax for all simulators.
- Simulation of the package is not necessary for frequencies < 100MHz.
For higher frequencies please add the wiring of the package equivalent circuit around the non-linear transistor.

Total power dissipation $P_{\text{tot}} = f(T_S)$

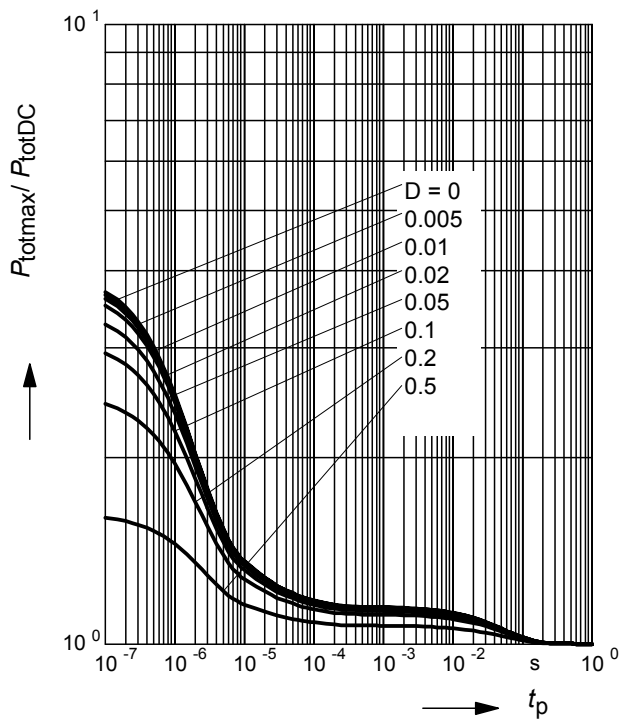


Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



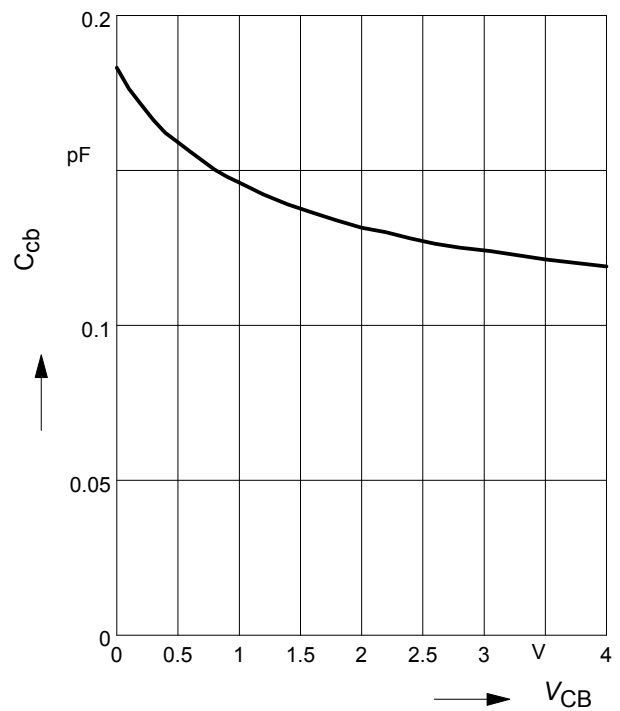
Permissible Pulse Load

$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$



Collector-base capacitance $C_{\text{cb}} = f(V_{\text{CB}})$

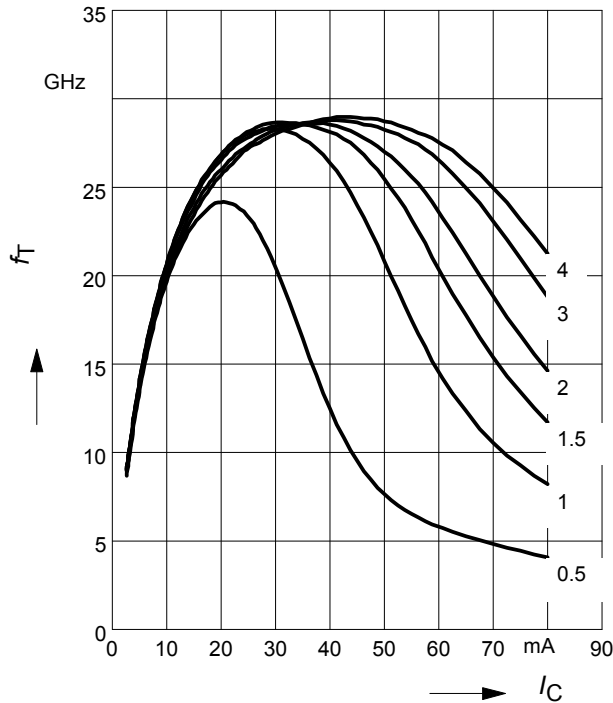
$f = 1\text{MHz}$



Transition frequency $f_T = f(I_C)$

$f = 1\text{GHz}$

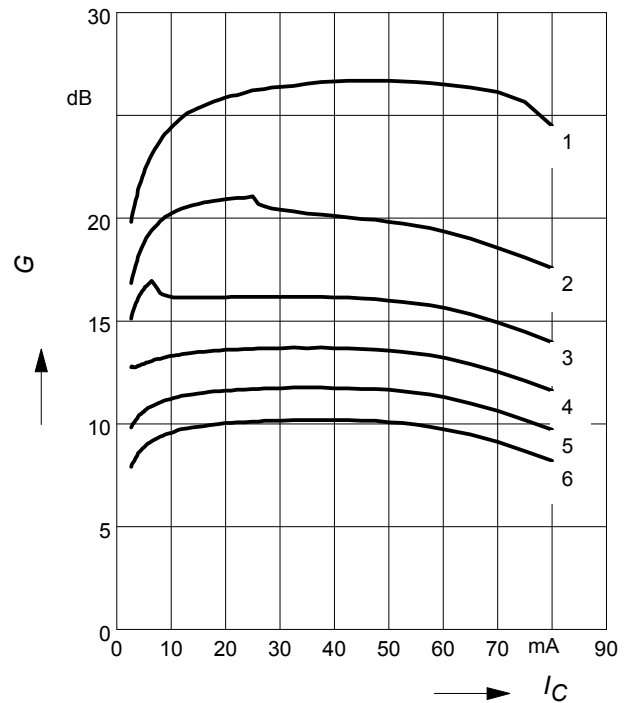
$V_{CE} = \text{Parameter in V}$



Power gain $G_{ma}, G_{ms} = f(I_C)$

$V_{CE} = 2\text{V}$

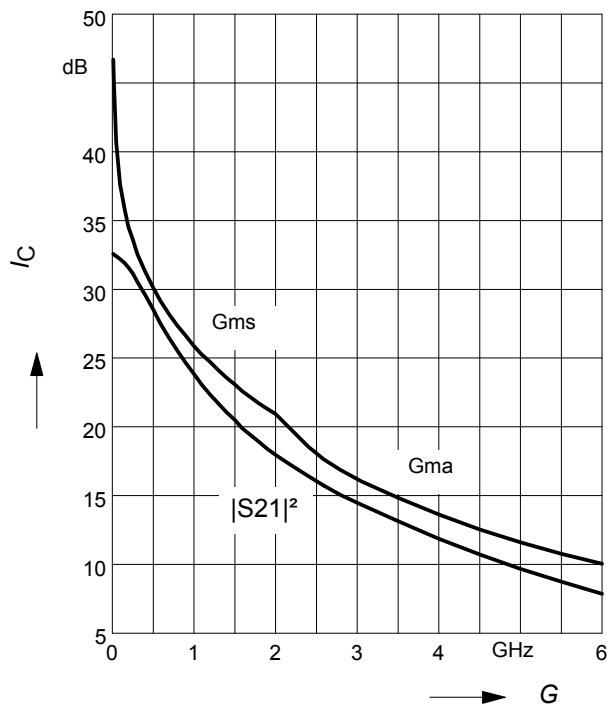
$f = \text{Parameter in GHz}$



Power Gain $G_{ma}, G_{ms} = f(f)$,

$|S_{21}|^2 = f(f)$

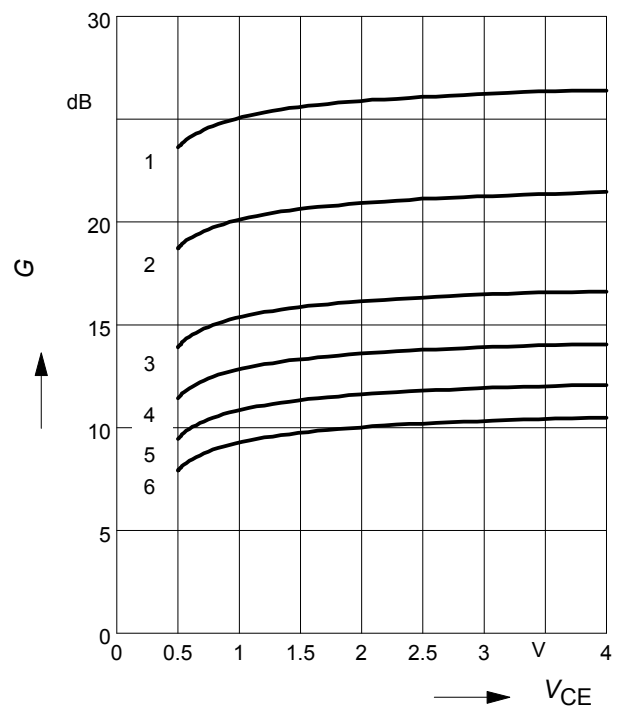
$V_{CE} = 2\text{V}, I_C = 20\text{mA}$



Power gain $G_{ma}, G_{ms} = f(V_{CE})$

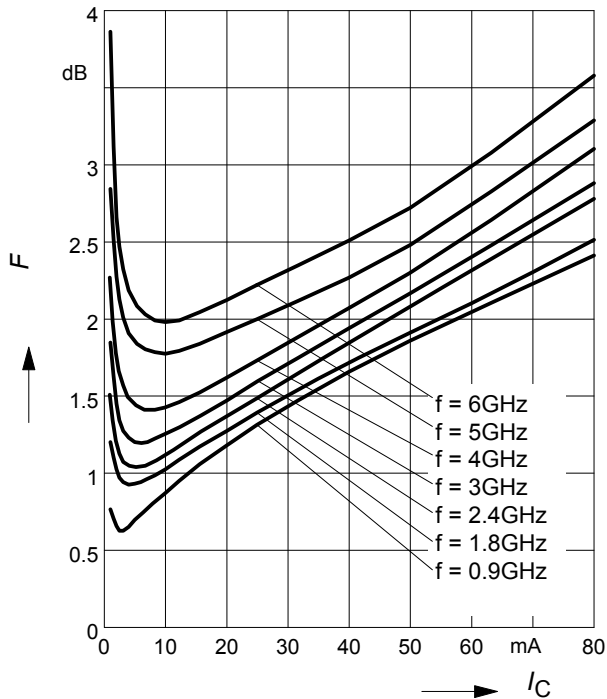
$I_C = 20\text{mA}$

$f = \text{Parameter in GHz}$



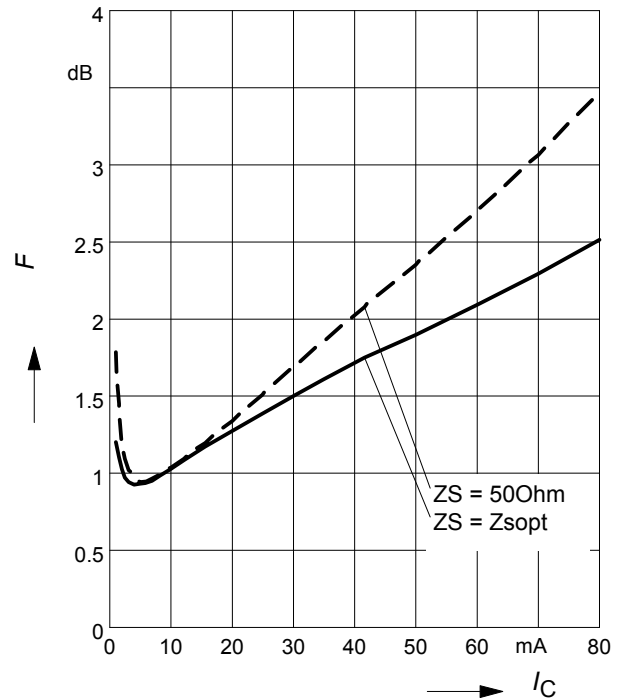
Noise figure $F = f(I_C)$

$V_{CE} = 2V, Z_S = Z_{Sopt}$



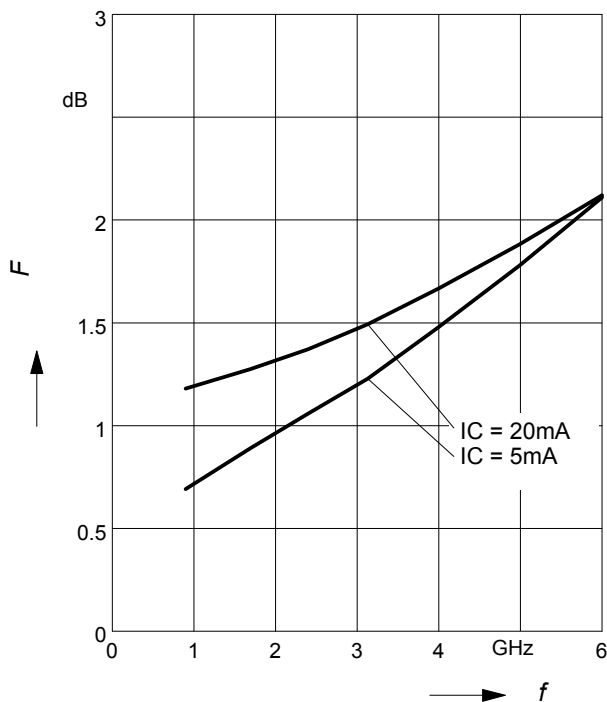
Noise figure $F = f(I_C)$

$V_{CE} = 2V, f = 1.8\text{GHz}$



Noise figure $F = f(f)$

$V_{CE} = 2V, Z_S = Z_{Sopt}$



Source impedance for min.

noise figure vs. frequency

$V_{CE} = 2V, I_C = 5\text{mA} / 20\text{mA}$

